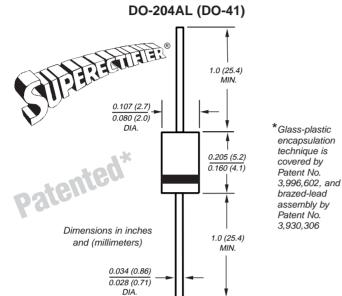


New Product

Vishay Semiconductors formerly General Semiconductor

Glass Passivated Ultrafast Rectifier

Reverse Voltage 600V Forward Current 1.0A



Features

- High temperature metallurgically bonded construction
- · Cavity-free glass passivated junction
- Ultrafast recovery time for high efficiency
- · Low forward voltage, high current capability
- Capable of meeting environmental standards of MIL-S-19500
- Hermetically sealed package
- Low leakage current High surge current capability
- · Specified reverse surge capability
- High temperature soldering guaranteed: 350°C/10 seconds, 0.375" (9.5mm) lead length,5 lbs. (2.3kg) tension

Mechanical Data

Case: JEDEC DO-204AL, molded plastic over glass body

Terminals: Plated axial leads, solderable per

MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any Weight: 0.012 oz., 0.3 g

Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	VRRM	600	V
Maximum RMS voltage	VRMS	420	V
Maximum DC blocking voltage	V _{DC}	600	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at T _L = 85°C (See Fig. 1)	I _{F(AV)}	1.0	А
Peak forward surge current 10ms single half sine-wave superimposed on rated load	IFSM	30	А
Non repetitive peak reverse energy (Note 1)	ERSM	5	mJ
Typical thermal resistance (Note 2,3)	R⊕JA R⊕JL	70 16	°C/W
Operating junction and storage temperature range	TJ, TSTG	-65 to +175	°C

Electrical Characteristics (TA = 25°C unless otherwise noted)

Minimum avalanche breakdown voltage at 100μA	VBR	600	V
Maximum instantaneous $T_J = 25^{\circ}C$ forward voltage at 1.0A $T_J = 175^{\circ}C$	VF	2.5 1.3	V
Maximum DC reverse current $T_A = 25^{\circ}C$ at rated DC blocking voltage $T_A = 165^{\circ}C$	IR	5.0 150	μΑ
Max. reverse recovery time at IF = 0.5A, IR = 1.0A, Irr	= 0.25A t _{rr}	30	ns
Maximum junction capacitance at 4.0V, 1MHz	CJ	45	pF
Maximum reverse recovery current slope at $I_F = 1A$, $V_R = 30V$, $di_f/dt = -1A/\mu s$	di _r /dt	7	A/µs

Notes: (1) Peak reverse energy measured with 8/20µs surge

(2) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, mounted on P.C.B. with 0.5 x 0.5" (12 x 12mm) copper pads

(3) Thermal resistance from junction to lead at 0.375" (9.5mm) lead length with both leads attached to heatsink

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Ratings and

Characteristic Curves (TA = 25°C unless otherwise noted)

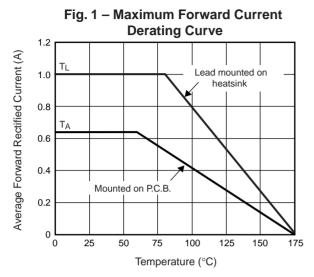


Fig. 3 - Typical Instantaneous **Forward Characteristics**

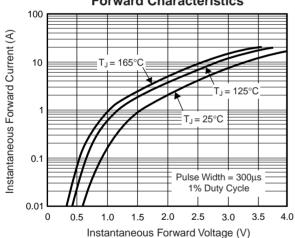


Fig. 5 - Typical Junction Capacitance

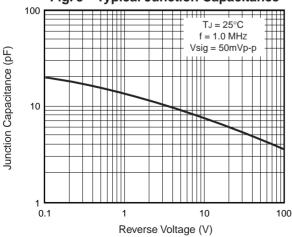


Fig. 2 - Maximum Non-Repetitive Peak **Forward Surge Current**

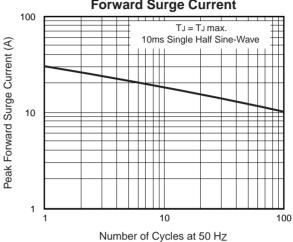


Fig. 4 - Typical Reverse Leakage Characteristics

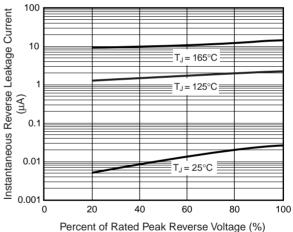
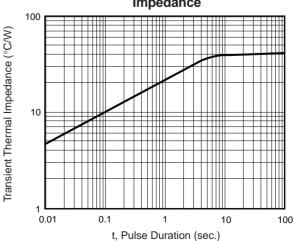


Fig. 6 - Typical Transient Thermal **Impedance**



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